

Description

The CYTLP521 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode, The CYTLP521 offer sigal isolated channels in an eight lead plastic DIP , DIP-M or SMD package.

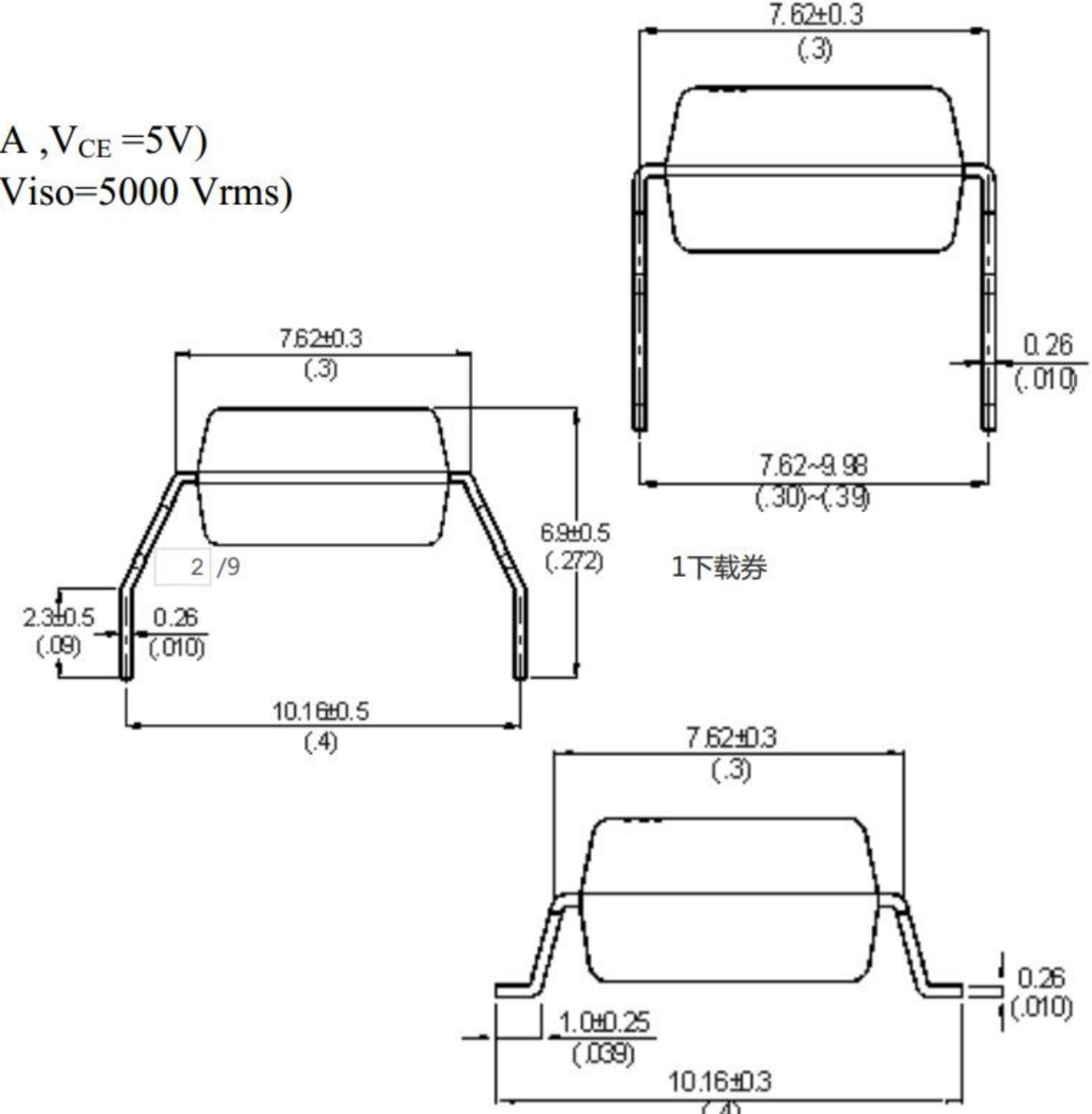
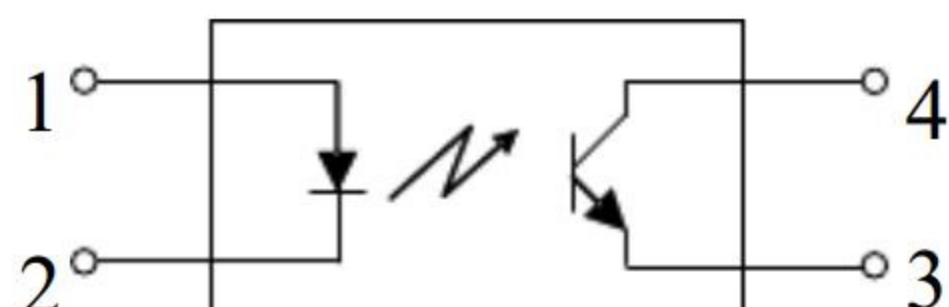
Features

- Current transfer ratio (CTR: 130~600% at $I_F=5mA, V_{CE}=5V$)
- High isolation voltage between input and output ($V_{iso}=5000V_{rms}$)
- Minimum BV_{CEO} of 80V guaranteed

Applications

- Switching power supply, intelligent meter
- Industrial control, measuring instruments
- Office equipment such as copiers
- Household appliances, such as air conditioners, fans, water heaters, etc.

Block Diagram and Package



Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward Current	I_F	50	mA
	Reverse Voltage	V_R	6	V
	Power Dissipation	P	70	mW
Output	Collector Power Dissipation	P_C	150	mW
	Collector Current	I_C	50	mA
	Collector-Emitter Voltage	V_{CEO}	80	V
	Emitter-Collector Voltage	V_{ECO}	7	V
Total Power Dissipation		P_{tot}	200	mW
Isolation Voltage		V_{iso}	5000	V_{rms}
Operating Temperature		T_{opr}	-55~+110	°C
Storage Temperature		T_{stg}	-55~+125	°C
Soldering Temperature		T_{sol}	260	°C

Electro-optical Characteristics (Ta=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V_{F1}	$I_F=10mA$	1.0	-	1.3	V
	Forward Voltage	V_{F2}	$I_F=20mA$	1.1	-	1.4	V
	Reverse Current	I_R	$V_R=5V$	-	-	10	μA
	Terminal Capacitance	C_t	$V=0, f=1kHz$	-	30	250	pF
Output	Collector Dark Current	I_{CEO}	$V_{CE}=50V$	-	-	100	nA
	Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=0.1mA, I_F=0$	80	-	-	V
	Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=10\mu A, I_F=0$	7	-	-	V
Transfer Characteristics	Current Transfer Ratio	CTR	$I_F=5mA, V_{CE}=5V$	130	-	600	%
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F=2mA, I_C=5mA$	-	0.25	0.8	V
	Isolation Resistance	R_{ISO}	DC5000V, 40~60%R.H.	1×10^{12}	-	-	Ω
	Floating Capacitance	C_f	$V=0, f=1MHz$	-	0.6	1.0	pF
	Cut-off Frequency	F_c	$V_{CE}=5V, I_C=2mA, R_L=100\Omega, -3dB$	-	80	-	kHz
Switching Characteristics	Rise Time	T_r	$V_{CE}=10V, I_C=2mA, R_L=100\Omega$	-	2	-	μs
	Fall Time	T_f		-	3	-	μs
	Turn On Time	T_{on}		-	3	-	μs
	Turn Off Time	T_{off}		-	3	-	μs
	Turn On Time	T_{on}	$R_L = 1.9 k\Omega, V_{CC} = 5 V, I_F = 16 mA$	-	2	-	μs
	Storage time	T_s		-	15	-	μs
	Turn Off Time	T_{off}		-	25	-	μs

* CTR= $I_C/I_F \times 100\%$

Rank Table of CTR

Type	Classification	Current Transfer Ratio (%) (I_C/I_F)		Marking Of Classification
		$I_F = 5mA, V_{CE} = 5V, T_a = 25^\circ C$		
		Min	Max	
CYTLP521	A	50	600	
	Rank Y	50	150	
	Rank GR	100	300	
	Rank BL	200	600	
	Rank GB	100	600	

Fig.1 Test Circuits

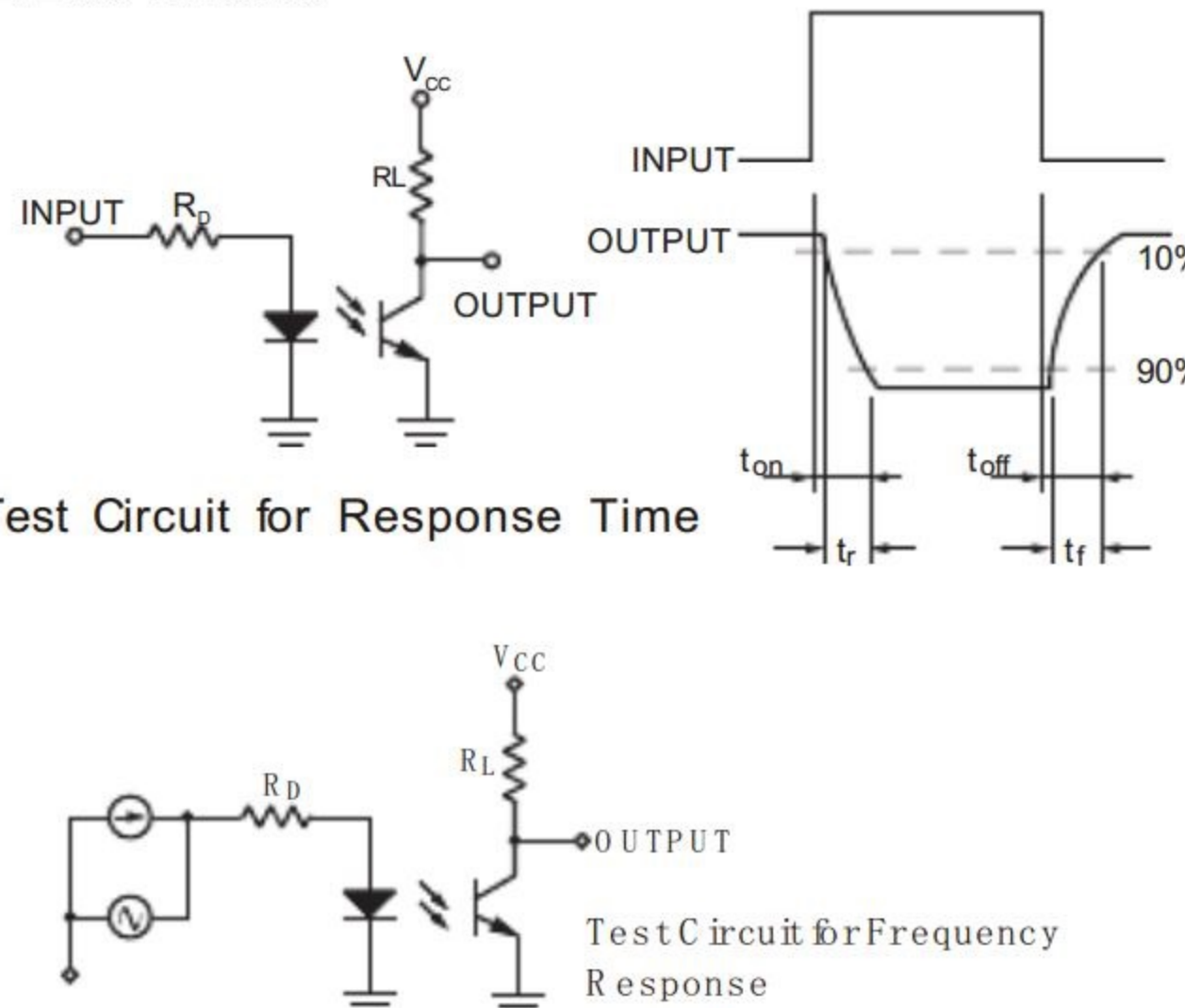


Fig.3 Forward Current vs. Forward Voltage

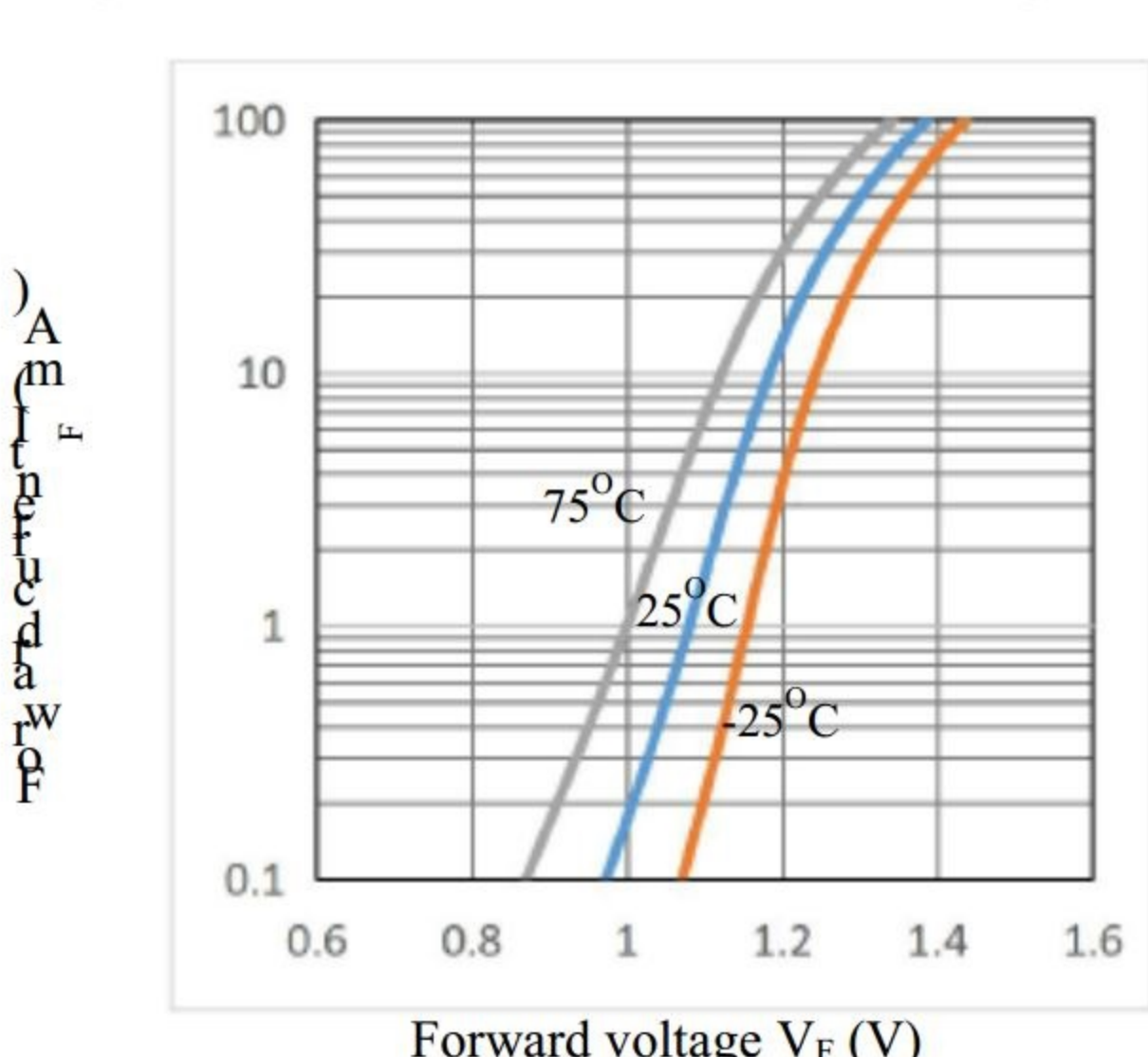


Fig.2 Current Transfer Ratio vs. Forward Current

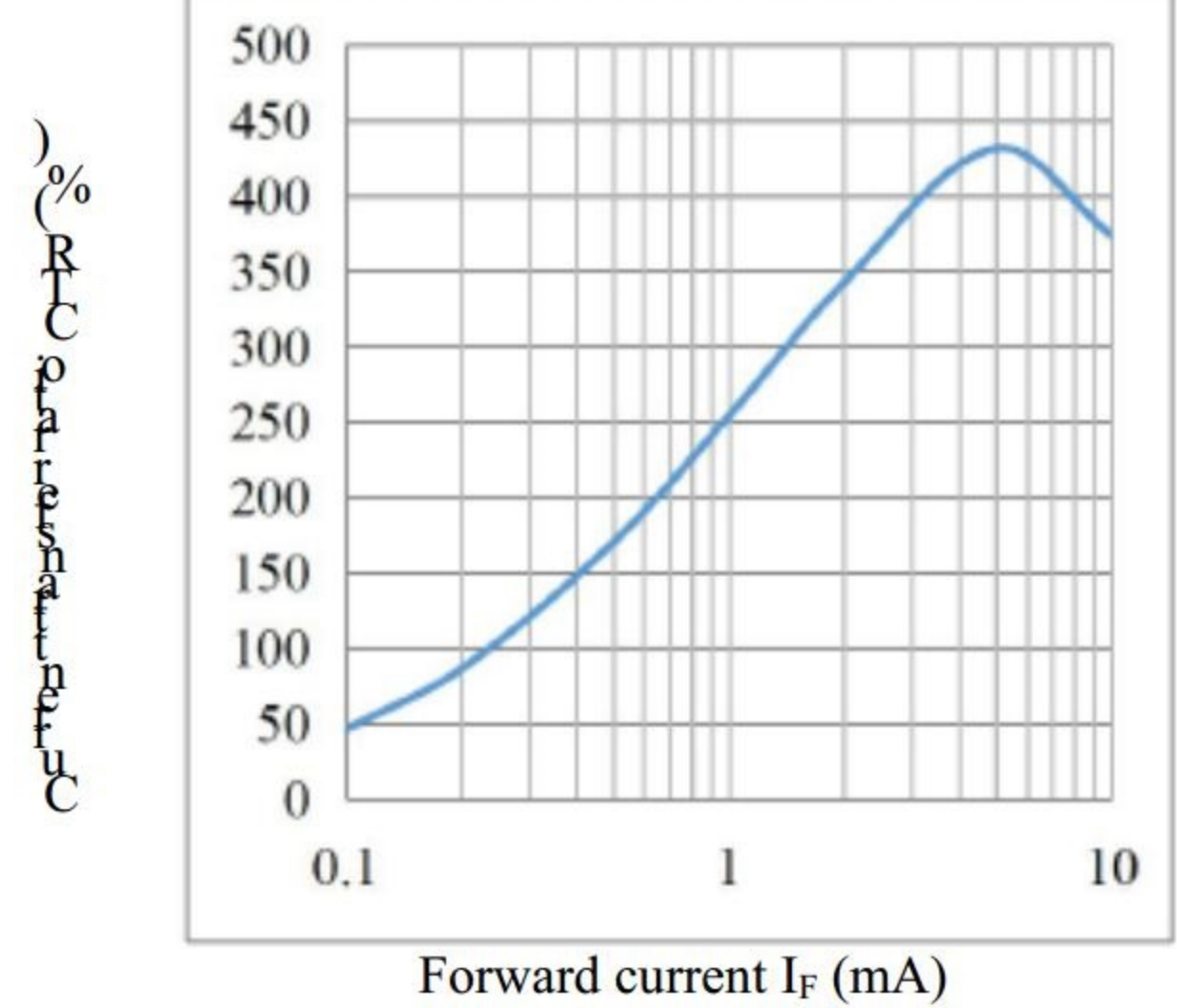


Fig.4 Collector Current vs. Collector-emitter Voltage

